



Pietro della Casa (Autor)

## Two-step MOVPE, in-situ etching and buried implantation: applications to the realization of GaAs laser diodes

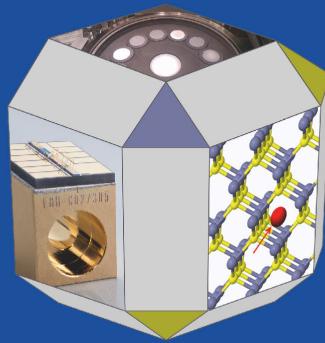


**63**

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Two-step MOVPE, in-situ etching and  
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